

## D. Thin Film Process Technology 분과

2020년 2월 14일(금), 15:45-17:30 / Room J (하트 III, 6층)

### ■ [FJ3-D] Memory Devices

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<b>FJ3-D-1</b> 15:45-16:15	<b>[초청]</b> <b>Three-Terminal Memristor</b> Hong-Sub Lee <i>Kangwon National University</i>
<b>FJ3-D-2</b> 16:15-16:45	<b>[초청]</b> <b>Atomic Layer Deposition of SrTiO<sub>3</sub> Thin Films for Dynamic Random Access Memory Capacitors</b> Woongkyu Lee <i>Department of Electrical Engineering, Myongji University</i>
<b>FJ3-D-3</b> 16:45-17:00	<b>CVD NbSe<sub>2</sub> Buffer Layer to Control Active Metal Ions in Ag/NbSe<sub>2</sub>/HfO<sub>2</sub>/Pt Device for Stable Synaptic Functions</b> Yu-Rim Jeon <sup>1</sup> , Yonghun Kim <sup>2</sup> , and Changhwan Choi <sup>1</sup> <i><sup>1</sup>Division of Materials Science and Engineering, Hanyang University, <sup>2</sup>Surface Technology Division, KIMS</i>
<b>FJ3-D-4</b> 17:00-17:15	<b>Synaptic and Nonvolatile Memory Characteristics in Ag/HfO<sub>2</sub>/Pt Structured Conductive Bridge Random Access Memory Devices</b> Haider Abbas and Changhwan Choi <i>Division of Materials Science and Engineering, Hanyang University</i>
<b>FJ3-D-5</b> 17:15-17:30	<b>Mechanically Stretchable Charge-Trap Memory Transistors Fabricated on Ultra-Thin Polyimide Film with Wavy Dimensional Structures</b> Hyo-Eun Kim, Hye-Won Jang, and Sung-Min Yoon <i>Department of Advanced Materials Engineering for Information and Electronics, Kyung Hee University</i>